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•••				First Named Inventor	TASHIRO		
STA	TEMENT B	Y AP	PLICANI	Group Art Unit	Unassigned		
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<del></del>	OTHER - NON PATENT LITERATURE DOCUMENTS  Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item			
Examiner Initials	Doc. No.	(book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number (s), publisher, city and/or country where published.	Yes	No*+
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Date Considered Examiner Signature

A concise statement of relevance is being submitted in lieu of a translation. 37 CFR 1.98(a)(3).
 An English-language equivalent/patent, or an English-language abstract, or an English-language version of the search report or action by a foreign patent office in a counterpart foreign application indicating the degree of relevance found by the foreign office is being submitted in lieu of a concise explanation of relevance under 37 CFR 1.98(a)(3).